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1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 10 A
- Reverse voltage: V_R ≤ 45 V
- Low forward voltage
- · High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

3. Applications

- · Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|-------------------------|--|-----|-----|-----|------|
| I _{F(AV)} | average forward current | δ = 0.5; f = 20 kHz; $T_{sp} \le 130$ °C; square wave | - | - | 10 | А |
| V_R | reverse voltage | T _j = 25 °C | - | - | 45 | V |
| V _F | forward voltage | I_F = 10 A; $t_p \le 300 \mu s$; δ ≤ 0.02; T_j = 25 °C; pulsed | - | 473 | 540 | mV |
| I _R | reverse current | $V_R = 10 \text{ V; } t_p \le 3 \text{ ms; } \delta = 0.3;$ $T_j = 25 ^{\circ}\text{C; pulsed}$ | - | 13 | 30 | μΑ |
| | | $V_R = 45 \text{ V; } t_p \le 3 \text{ ms; } \delta = 0.3;$ $T_j = 25 \text{ °C; pulsed}$ | - | 150 | 500 | μΑ |





5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | Α | anode | | K PA |
| 2 | Α | anode | 3 | aaa-009063 |
| 3 | K | cathode | 2 | |
| | | | CFP15 (SOT1289) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | е | | | | |
|--------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMEG45A10EPD | CFP15 | plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm | SOT1289 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| PMEG45A10EPD | 4510 AAAA |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|-----|------|
| V_R | reverse voltage | T _j = 25 °C | | - | 45 | V |
| I _F | forward current | T _{sp} = 125 °C; δ = 1 | | - | 14 | Α |
| I _{F(AV)} | average forward current | δ = 0.5; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave | | - | 10 | Α |
| I _{FSM} | non-repetitive peak forward current | t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave | | - | 170 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 0.9 | W |
| | | | [2] | - | 1.2 | W |
| | | | [3] | - | 3 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |

PMEG45A10EPD

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| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------|------------|-----|-----|------|
| T _{stg} | storage temperature | | -65 | 150 | °C |

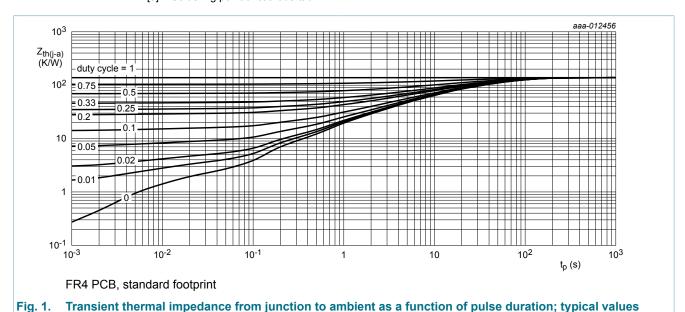
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|-------------|--------|-----|-----|-----|------|
| R _{th(j-a)} thermal resistance from junction to ambient | | in free air | [1][2] | - | - | 165 | K/W |
| | | [1][3] | - | - | 120 | K/W | |
| | ambient | | [1][4] | - | - | 50 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | [5] | - | - | 4 | K/W |

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



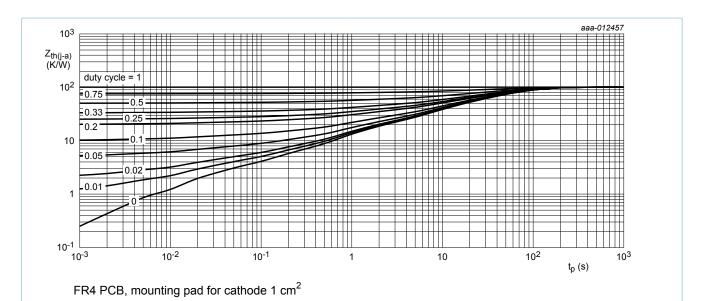


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

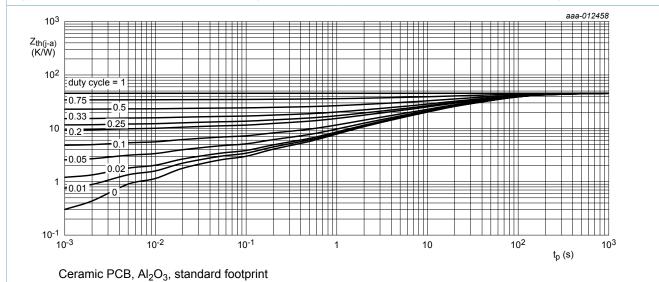
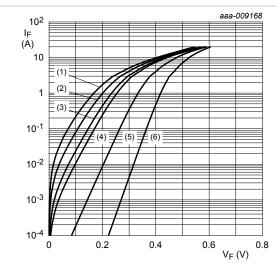


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------------|---------------------------------------|--|-----|-----|-----|------|
| V _F | forward voltage | I_F = 1 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed | - | 330 | 380 | mV |
| | | I_F = 2 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed | - | 357 | - | mV |
| | | I_F = 3 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed | - | 377 | - | mV |
| | | I_F = 5 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed | - | 409 | 470 | mV |
| | | I_F = 10 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed | - | 473 | 540 | mV |
| I _R reverse currer | reverse current | V_R = 5 V; t_p ≤ 3 ms; δ = 0.3; T_j = 25 °C; pulsed | - | 10 | - | μA |
| | | $V_R = 10 \text{ V; } t_p \le 3 \text{ ms; } \delta = 0.3;$ $T_j = 25 ^{\circ}\text{C; pulsed}$ | - | 13 | 30 | μA |
| | | $V_R = 30 \text{ V}; t_p \le 3 \text{ ms}; \delta = 0.3;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$ | - | 36 | - | μA |
| | | V_R = 45 V; $t_p \le 3$ ms; $\bar{\delta}$ = 0.3; T_j = 25 °C; pulsed | - | 150 | 500 | μA |
| | | $V_R = 10 \text{ V; } t_p \le 3 \text{ ms; } \bar{\delta} = 0.3;$ $T_j = 125 \text{ °C; pulsed}$ | - | 11 | - | mA |
| C _d | diode capacitance | V _R = 1 V; f = 1 MHz; T _j = 25 °C | - | 715 | - | pF |
| | | V _R = 10 V; f = 1 MHz; T _j = 25 °C | - | 240 | - | pF |
| t _{rr} | reverse recovery time ; step recovery | $I_F = 0.5 \text{ A}$; $I_R = 0.5 \text{ A}$; $I_{R(meas)} = 0.1 \text{ A}$; $I_{j} = 25 \text{ °C}$ | - | 21 | - | ns |
| t _{rr} | reverse recovery time ; ramp recovery | $dI_F/dt = 200 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}; I_F = 6 \text{ A};$ $V_R = 26 \text{ V}$ | - | 13 | - | ns |
| V _{(BR)R} | reverse breakdown voltage | I_R = 5 mA; T_j = 25 °C; t_p ≤ 1.2 ms; δ = 0.12; pulsed | 45 | - | - | V |
| V_{FRM} | peak forward recovery voltage | $I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$ | - | 317 | - | mV |



(1)
$$T_j = 150 \, ^{\circ}C$$

(2)
$$T_i = 125 \, ^{\circ}C$$

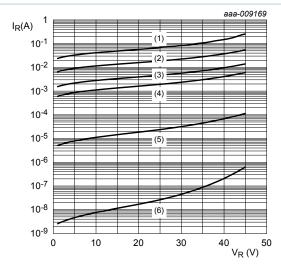
(3)
$$T_i = 100 \, ^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_i = 25 \,{}^{\circ}\text{C}$$

(6)
$$T_i = -40 \, ^{\circ}C$$

Fig. 4. Forward current as a function of forward voltage; typical values (pulsed condition)



(1)
$$T_i = 150 \, ^{\circ}\text{C}$$

(2)
$$T_j = 125 \,^{\circ}\text{C}$$

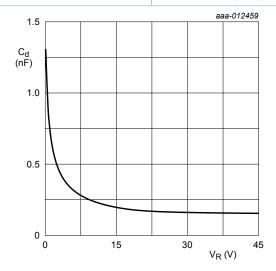
(3)
$$T_j = 100 \, ^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_i = 25 \, ^{\circ}C$$

(6)
$$T_i = -40 \, ^{\circ}C$$

Fig. 5. Reverse current as a function of reverse voltage; typical values (pulsed condition)



 $f = 1 MHz; T_{amb} = 25 °C$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values

11. Test information

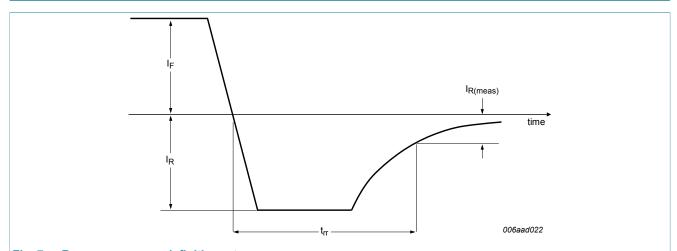


Fig. 7. Reverse recovery definition; step recovery

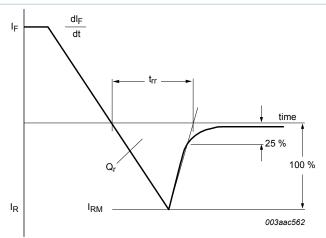


Fig. 8. Reverse recovery definition; ramp recovery

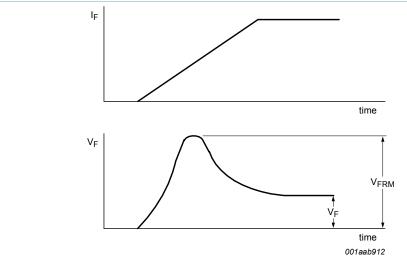
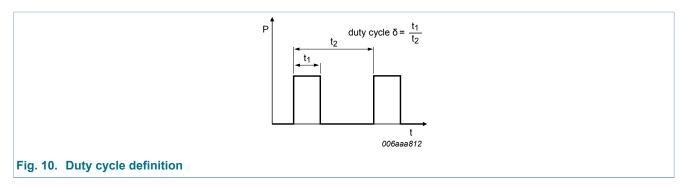


Fig. 9. Forward recovery definition

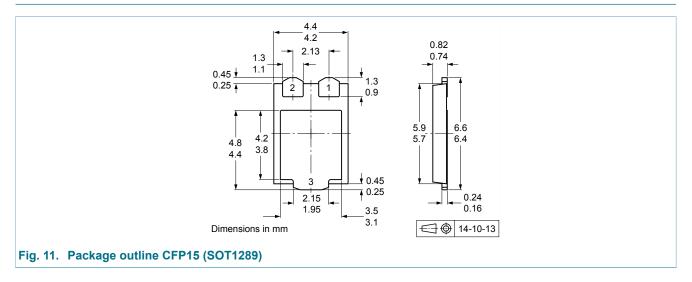
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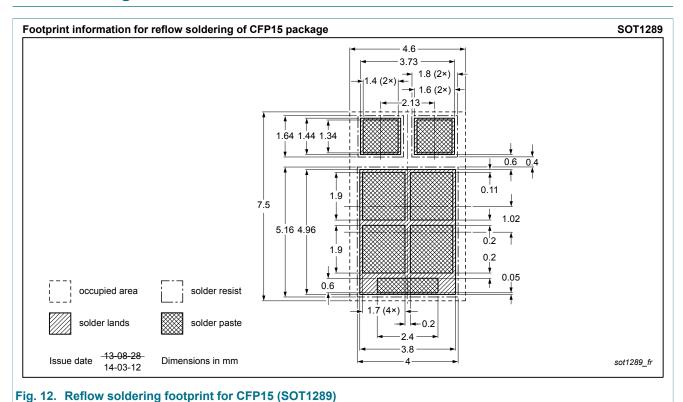


The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | |
|------------------|---------------------------------|----------------------|---------------|------------------|--|
| PMEG45A10EPD v.3 | 20141216 | Product data sheet | - | PMEG45A10EPD v.2 | |
| Modifications: | Package outline drawing updated | | | | |
| PMEG45A10EPD v.2 | 20140416 | Product data sheet | - | PMEG45A10EPD v.1 | |
| PMEG45A10EPD v.1 | 20140217 | Objective data sheet | - | - | |

15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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